

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	37	$^{\circ}C/W$
Soldering temperature, wave soldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2		-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance		$V_{GS}=-10V, I_D=-24A$				
		$V_{GS}=-4.5V, I_D=-12A$				
Forward Transconductance	g_{FS}	$V_{DS}=-25V, I_D=-10A$				
Source-drain voltage	V_{SD}	$I_S=-24A$				

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=20V$ $f = 1MHz$	-	4500	-	pF
Output capacitance	C_{oss}		-	398	-	
Reverse transfer capacitance	C_{rss}		-	157	-	

Gate Charge characteristics($T_a = 25$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
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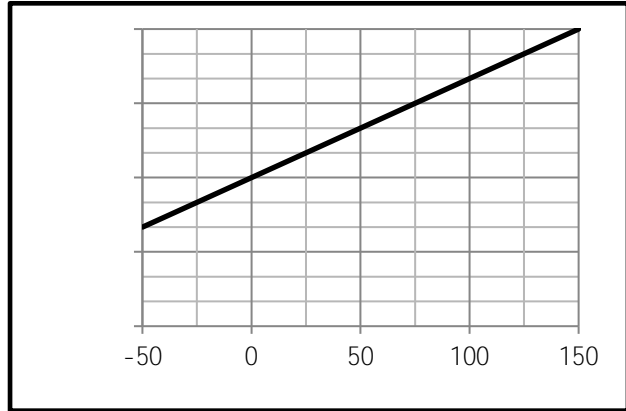
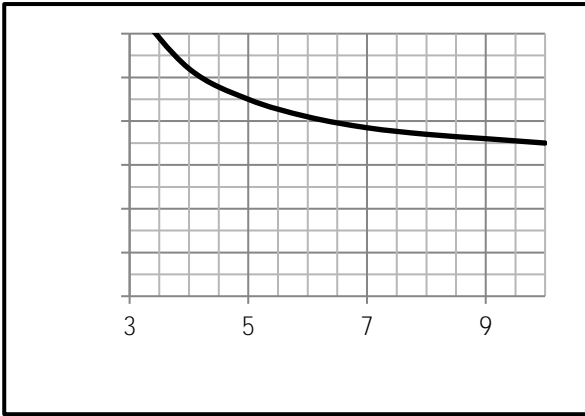


Fig.10 I_D -Junction Temperature

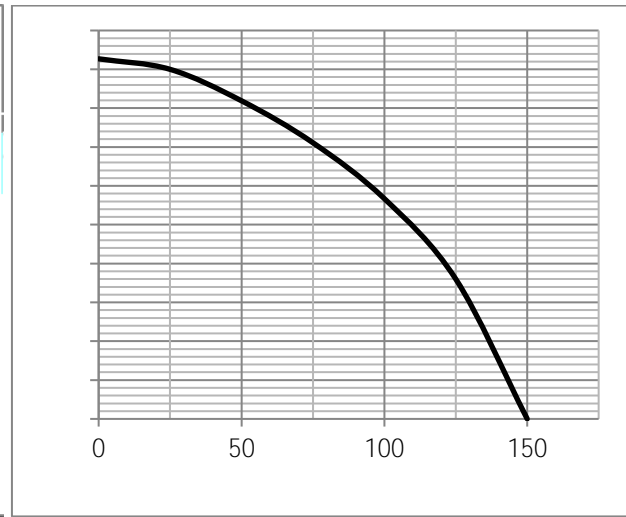
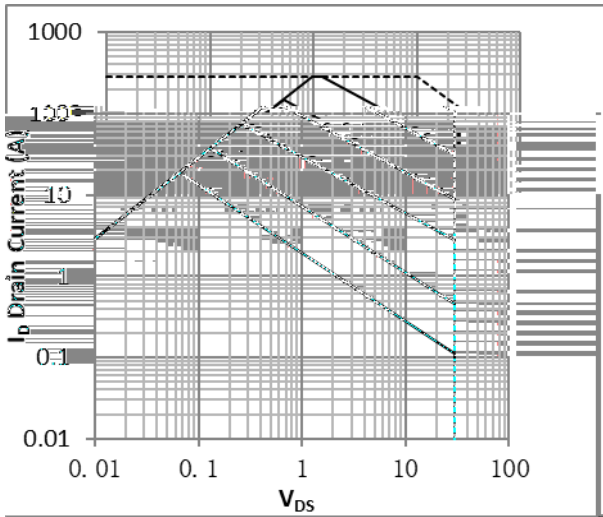


Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

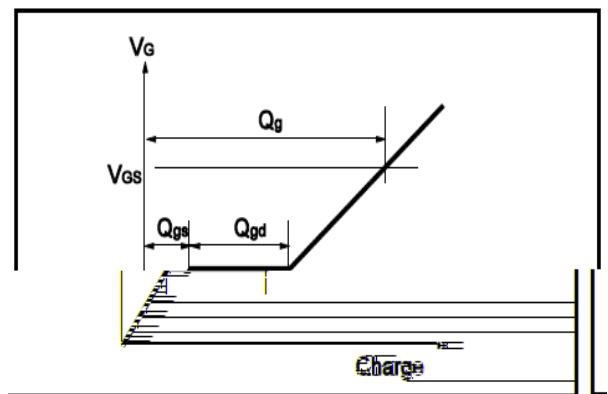
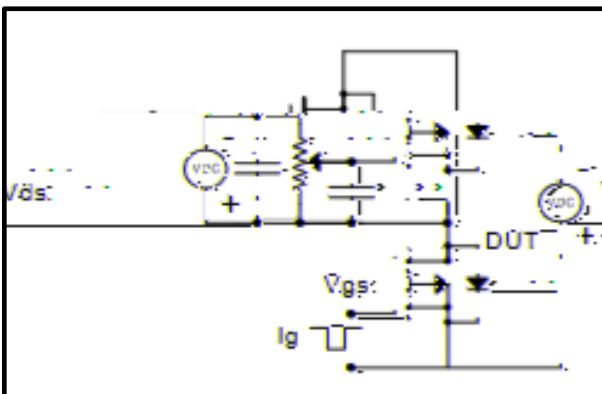


Fig.11 Switching Time Measurement Circuit

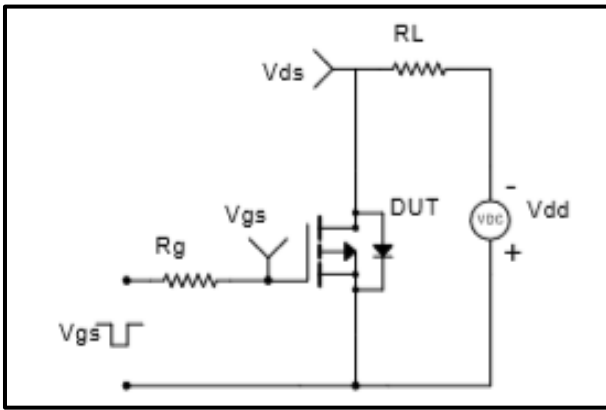
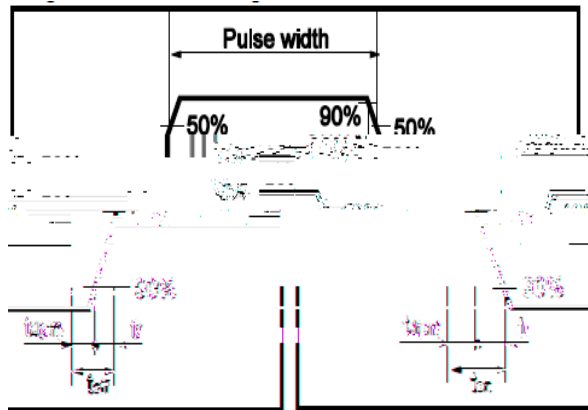


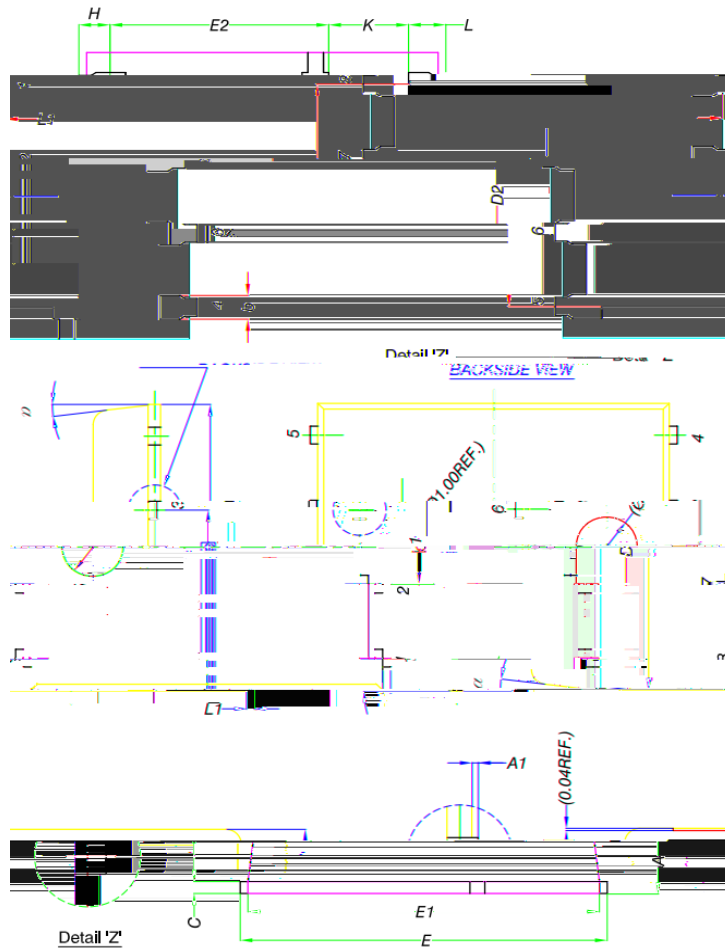
Fig.12 Gate Charge Waveform





sions DFN5x6

Unit mm



MILLIMETERS

D1	4.80	4.90	5.00
D2	3.67	3.81	3.96
	5.90	6.00	6.10
E1	5.20	5.28	5.36
e	1.27 BSC		
	0.41	0.51	0.61
	1.10		
		0.51	0.61
		0.51	0.61
			12°